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II. Amendments to the Specification

Please replace the paragraph beginning at the top of Page 6 under "Description of the Preferred Embodiments" and continuing onto Page 7 with the following amended paragraph:

Fig. 2 depicts a vertical cross section of a multiple element bipolar ESD protection device. The starting structure is a p doped substrate 10, typically created on a silicon wafer of 100 crystal orientation and with a doping level in the range of 10^{15} atoms per cubic centimeter (a/cm^3). A heavily doped n+ first semiconductor layer 12 called a buried layer or subcollector is formed upon the substrate typically using arsenic or antimony as impurity dopants ~~dopents~~ and using either a chemical diffusion or an ion implant process. An ion implant process typically uses an implant energy in the range of 30 KeV with a dosage of 10^{15} atoms per square centimeter (a/cm^2) to produce a n+ buried layer doping level between 10^{18} and 10^{19} a/cm^3. Next, a light to moderately doped n type epitaxial second semiconductor layer 14 is deposited with a doping level typically in the range of 10^{15} to 10^{16} a/cm^3 with arsenic frequently being used as the dopant ~~dopent~~ source element. A plurality of deep n+ regions 16 are implanted into the second semiconductor layer 14 beneath the collector contact regions 18 typically using either an arsenic, antimony or phosphorous dopant ~~dopent~~ with an implant energy in the range of 30 KeV with a dosage of 10^{15} a/cm^2 to produce an n+ ~~buried layer~~ region doping level between 10^{18} and 10^{19} a/cm^3. This provides a low resistance path to the surface conductor system 34 for the collector current. The structure processing is continued by implanting a third semiconductor layer 24 of p dopant ~~dopent~~, usually boron, with an implant energy in the range of 30 KeV with a dosage of